



UL;E76102 (M)

SanRex IGBT Module **GAE100BA60** is designed for high speed, high current switching applications. This Module is electrically isolated and contains IGBT connected with clamp diode in series, soft recovery diode ($t_{rr}=0.1\mu s$) reverse connected across IGBT.

● $I_C=100A$ $V_{CES}=600V$

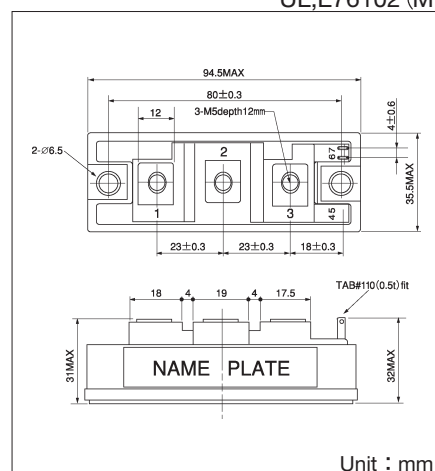
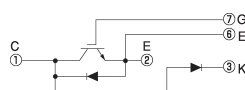
● $V_{CES(sat)}=2.3V$ Typ

● $t_f=0.10\mu s$ Typ

● Soft recovery diode

(Applications)

Brake for motor control (VVVF)



Unit : mm

Maximum Ratings

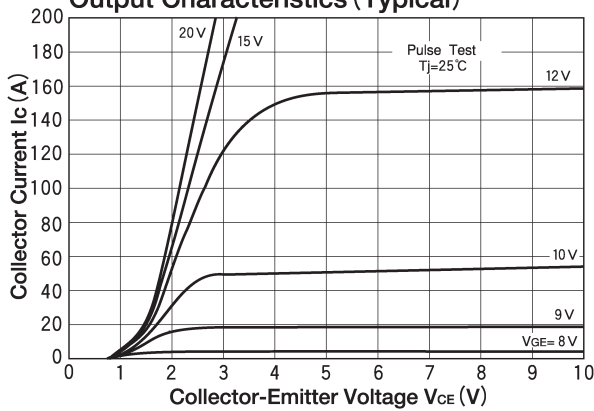
(Unless otherwise $T_j=25^\circ C$)

Symbol	Item		Conditions	Ratings	Unit
				GAE100BA60	
V_{CES}	Collector-Emitter Voltage		with gate terminal shorted to emitter	600	V
V_{GES}	Gate-Emitter Voltage		with collector shorted to emitter	± 20	V
I_C	Collector Current	DC		100	A
I_{CP}		Pulse (1 ms)		200	
$-I_C$	Reverse Collector Current			100	A
P_T	Total Power Dissipation		$T_c=25^\circ C$	400	W
T_j	Junction Temperature			150	$^\circ C$
T_{stg}	Storage Temperature			$-40 \sim +125$	$^\circ C$
V_{ISO}	Isolation Voltage (R.M.S.)		A.C. 1 minute	2500	V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N·m (kgf·cm)
		Terminal (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	
	Mass		Typical Value	210	g

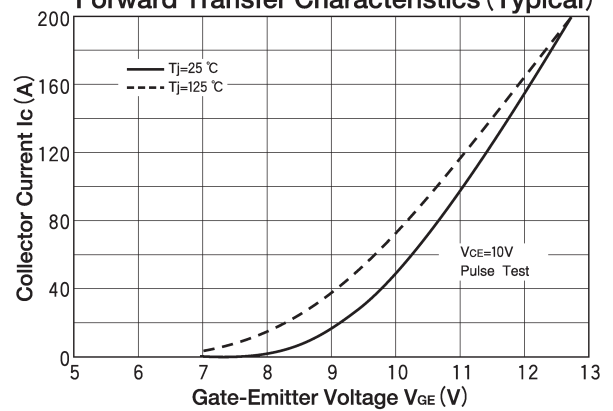
Electrical Characteristics

Symbol	Item		Conditions	Ratings			Unit
				Min.	Typ.	Max.	
I_{GES}	Gate Leakage Current		$V_{GE}=\pm 20V$, $V_{CE}=0V$			± 500	nA
I_{CES}	Collector Cut-Off Current		$V_{CE}=600V$, $V_{GE}=0V$			1.0	mA
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage		$V_{GE}=0V$, $I_C=1mA$	600			V
$V_{GE(th)}$	Gate Threshold Voltage		$V_{CE}=10V$, $I_C=10mA$	3.0		7.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C=100A$, $V_{GE}=15V$		2.3	2.8	V
C_{ies}	Input Capacitance		$V_{CE}=10V$, $V_{GE}=0V$, $f=1MHz$		7	10	nF
t_r	Switching Time	Rise Time	$I_C=100A$, $V_{GE}=+15V/-5V$ $V_{CC}=300V$, $R_G=6\Omega$		0.10	0.20	μs
$t_d(on)$		Turn-on Delay Time			0.20	0.40	
t_f		Fall Time			0.10	0.20	
$t_d(off)$		Turn-off Delay Time			0.40	0.80	
V_{ECS}	Emitter-Collector Voltage		$-I_C=100A$, $V_{GE}=0V$		2.00	2.80	V
t_{rr}	Reverse Recovery Time		$-I_C=100A$, $V_{GE}=-10V$, $di/dt=200A/\mu s$		0.1	0.15	μs
$R_{th(j-c)}$	Thermal Resistance		IGBT-Case			0.31	$^\circ C/W$
			Diode-Case			0.55	
V_{FM}	Forward Voltage Drop		$I_F=100A$, Clamp Diode		2.00	2.80	V
t_{rr}	Reverse Recovery Time		$I_F=100A$, $di_F/dt=-200A/\mu s$, Clamp Diode		0.1	0.15	μs
$R_{th(j-c)}$	Thermal Impedance		Clamp Diode			0.55	$^\circ C/W$

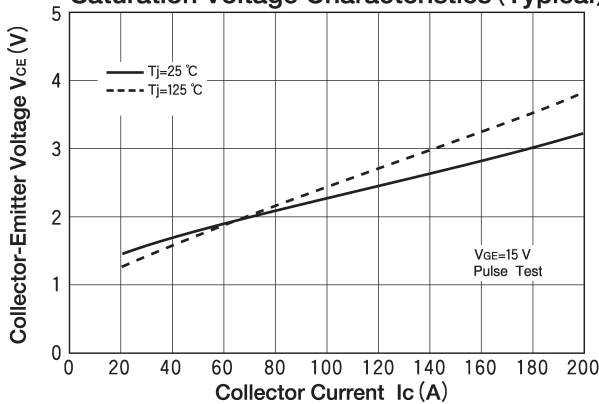
Output Characteristics (Typical)



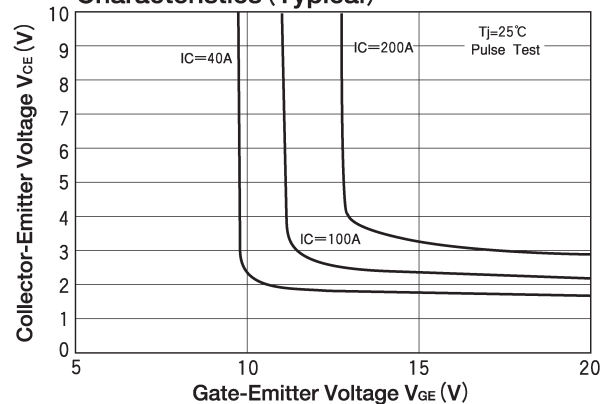
Forward Transfer Characteristics (Typical)



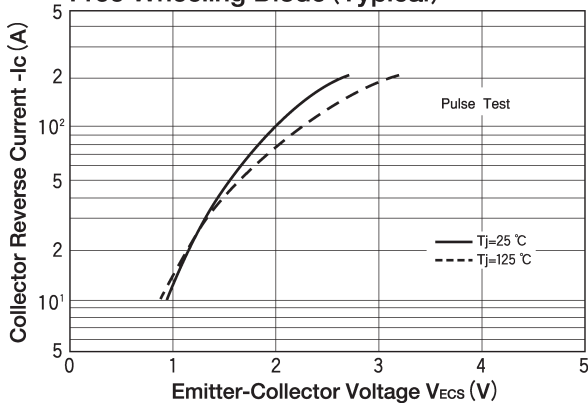
Saturation Voltage Characteristics (Typical)



Collector-Emmitter Saturation Voltage Characteristics (Typical)



Forward Voltage of Free Wheeling Diode (Typical)



Input Capacitance, Output Capacitance, Transfer Capacitance (Typical)

